# **Sensitive Gate Triacs Series**

## Silicon Bidirectional Thyristors

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO-92 package which is readily adaptable for use in automatic insertion equipment.

#### **Features**

- One-Piece, Injection-Molded Package
- Blocking Voltage to 600 V
- Sensitive Gate Triggering in Four Trigger Modes (Quadrants) for all
  possible Combinations of Trigger Sources, and especially for Circuits
  that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability
- Improved Noise Immunity (dv/dt Minimum of 10 V/µsec at 110°C)
- Commutating di/dt of 1.6 A/msec at 110°C
- High Surge Current of 8 A
- These are Pb-Free Devices

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage $(T_J = -40 \text{ to } +125^{\circ}\text{C})^{(1)}$ Sine Wave 50 to 60 Hz, Gate Open	V <sub>DRM,</sub> V <sub>RRM</sub>	600	V
On-State RMS Current Full Cycle Sine Wave 50 to 60 Hz (T <sub>C</sub> = +50°C)	I <sub>T(RMS)</sub>	1.0	Α
Peak Non-Repetitive Surge Current One Full Cycle, Sine Wave 60 Hz (T <sub>C</sub> = 110°C)	I <sub>TSM</sub>	8.0	Α
Circuit Fusing Considerations (t = 8.3 ms)	l <sup>2</sup> t	0.35	A <sup>2</sup> s
Average Gate Power ( $T_C = 80^{\circ}C$ , $t \le 8.3$ ms)	P <sub>G(AV)</sub>	1.0	W
Peak Gate Current (t $\leq$ 20 $\mu$ s, T <sub>J</sub> = +125°C)	I <sub>GM</sub>	1.0	Α
Operating Junction Temperature Range	TJ	-40 to +125	ô
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

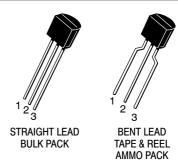


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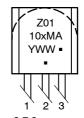
# TRIACS 1.0 AMPERE RMS 600 VOLTS





TO-92 (TO-226AA) CASE 029 STYLE 12

### MARKING DIAGRAM



x = 3,7,9
 Y = Year
 WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT		
1	Main Terminal 1	
2	Gate	
3	Main Terminal 2	

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	50	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	160	°C/W
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	$T_L$	260	°C

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

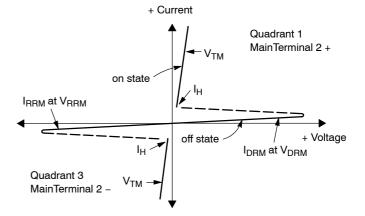
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
$ \begin{array}{ll} \text{Peak Repetitive Blocking Current} & T_J = 25^{\circ}\text{C} \\ \text{($V_D$ = Rated $V_{DRM}$, $V_{RRM}$; Gate Open)} & T_J = +125^{\circ}\text{C} \\ \end{array} $	I <sub>DRM</sub> , I <sub>RRM</sub>	- -	1 1	5.0 500	μΑ
ON CHARACTERISTICS					
Peak On–State Voltage ( $I_{TM} = \pm 1.4$ A Peak; Pulse Width $\leq 2.0$ ms, Duty Cycle $\leq 2.0\%$ )	V <sub>TM</sub>	-	_	1.56	V
Gate Trigger Current (Continuous dc) (Z0103MA) $ \begin{aligned} &(V_D=12\ Vdc,\ R_L=30\ \Omega) \\ &MT2(+),\ G(+) \\ &MT2(+),\ G(-) \\ &MT2(-),\ G(-) \\ &MT2(-),\ G(+) \end{aligned} $	I <sub>GT</sub>	0.15 0.15 0.15 0.25	- - -	3.0 3.0 3.0 5.0	mA
Gate Trigger Current (Continuous dc) (Z0107MA) $ \begin{aligned} &(V_D=12\ Vdc,\ R_L=30\ \Omega) \\ &MT2(+),\ G(+) \\ &MT2(+),\ G(-) \\ &MT2(-),\ G(-) \\ &MT2(-),\ G(+) \end{aligned} $	I <sub>GT</sub>	0.15 0.15 0.15 0.25	- - - -	5.0 5.0 5.0 7.0	mA
Gate Trigger Current (Continuous dc) (Z0109MA) $ \begin{aligned} &(V_D=12\ Vdc,\ R_L=30\ \Omega) \\ &MT2(+),\ G(+) \\ &MT2(+),\ G(-) \\ &MT2(-),\ G(-) \\ &MT2(-),\ G(+) \end{aligned} $	I <sub>GT</sub>	0.15 0.15 0.15 0.25	- - -	10 10 10 10	mA
Latching Current ( $V_D$ = 12 V, $I_G$ = 1.2 x $I_{GT}$ ) (Z0103MA) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	Ιι	- - -	- - -	7.0 15 7.0 7.0	mA
Latching Current ( $V_D$ = 12 V, $I_G$ = 1.2 x $I_{GT}$ ) (Z0107MA) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	Ιι	- - - -	- - -	10 20 10 10	mA
Latching Current ( $V_D$ = 12 V, $I_G$ = 1.2 x $I_{GT}$ ) (Z0109MA) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	Ιι	- - - -	1 1 1 1	15 25 15 15	mA
Gate Trigger Voltage (Continuous dc) (Z0103MA, Z0107MA, Z0109MA) ( $V_D$ = 12 Vdc, $R_L$ = 30 $\Omega$ ) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	V <sub>GT</sub>	- - - -	1 1 1	1.3 1.3 1.3 1.3	V
Gate Non–Trigger Voltage (Z0103MA, Z0107MA, Z0109MA) (V <sub>D</sub> = 12 V, R <sub>L</sub> = 30 $\Omega$ , T <sub>J</sub> = 125°C) All Four Quadrants	V <sub>GD</sub>	0.2	-	1.3	V
Holding Current (Z0103MA) (V <sub>D</sub> = 12 Vdc, Initiating Current = 50 mA, Gate Open) (Z0107MA, Z0109MA)	I <sub>H</sub>	- -	- -	7.0 10	mA

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

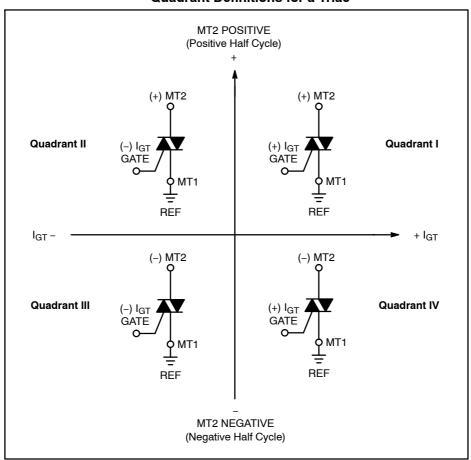
Characteristic			Min	Тур	Max	Unit
DYNAMIC CHARACTERISTICS						
Rate of Change of Commutating Current ( $V_D$ = 400 V, $I_{TM}$ = 0.84 A, Commutating dv/dt = 1.5 V/ $\mu$ s, Gate Open, $T_J$ = 110°C, f = 250 Hz, with Snubber)		di/dt(c)	1.6	_	-	A/ms
Critical Rate of Rise of Off–State Voltage ( $V_D$ = 67% Rated $V_{DRM}$ , Exponential Waveform, Gate Open, $T_J$ = 110°C)	Z0103MA Z0107MA Z0109MA	dv/dt	10 20 50	30 60 75	- - -	V/µs
Repetitive Critical Rate of Rise of On–State Current, $T_J$ = 125°C Pulse Width = 20 $\mu$ s, IPK <sub>max</sub> = 15 A, diG/dt = 1 A/ $\mu$ s, f = 60 Hz		di/dt	_	_	20	A/μs

# Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

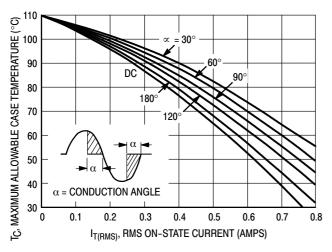


### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



= 30° 100 T(RMS), MAXIMUM ALLOWABLE AMBIENT TEMPERATURE (°C) 90 80 70 60 50 40 30 20 0.05 0.1 0.15 0 0.2 0.25 0.3 0.35 0.4  $I_{T(RMS)}$ , RMS ON-STATE CURRENT (AMPS)

Figure 1. RMS Current Derating

Figure 2. RMS Current Derating

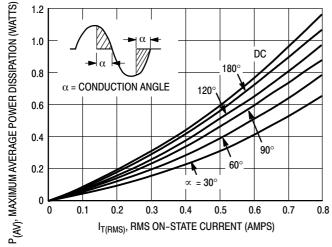


Figure 3. Power Dissipation

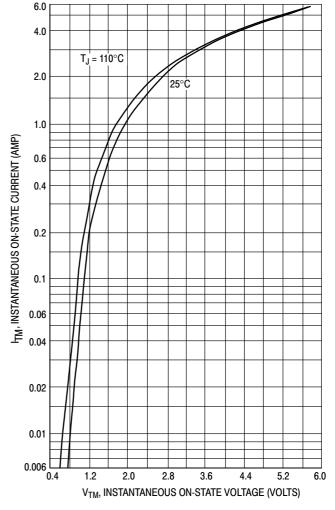
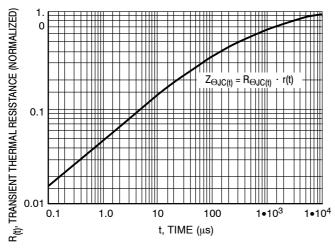


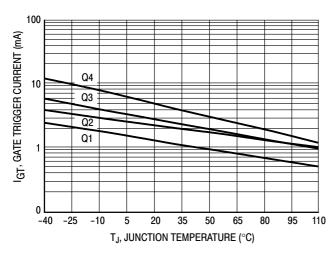
Figure 4. On-State Characteristics



TSM, PEAK SURGE CURRENT (AMPS) 5.0 3.0  $T_J = 110^{\circ}C$ 2.0 f = 60 Hz 1.0 1.0 10 30 50 100 2.0 3.0 5.0 NUMBER OF CYCLES

Figure 5. Transient Thermal Response

Figure 6. Maximum Allowable Surge Current



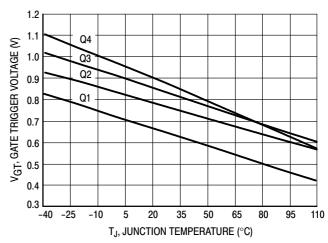
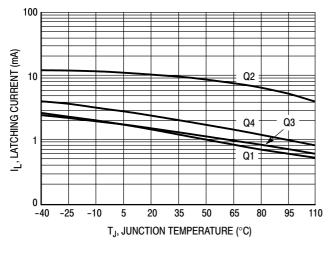


Figure 7. Typical Gate Trigger Current versus Junction Temperature

Figure 8. Typical Gate Trigger Voltage versus
Junction Temperature



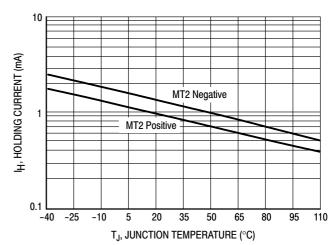
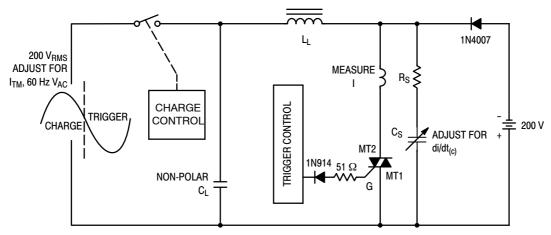


Figure 9. Typical Latching Current versus Junction Temperature

Figure 10. Typical Holding Current versus Junction Temperature



Note: Component values are for verification of rated  $(di/dt)_c$ . See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)<sub>c</sub>

## TO-92 EIA RADIAL TAPE IN FAN FOLD BOX OR ON REEL

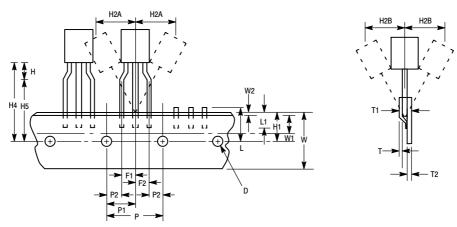


Figure 12. Device Positioning on Tape

		Specification				
			Inches		neter	
Symbol	ltem	Min	Max	Min	Max	
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2	
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51	
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8	
Н	Bottom of Component to Seating Plane	0.059	0.156	1.5	4.0	
H1	Feedhole Location	0.3346	0.3741	8.5	9.5	
H2A	Deflection Left or Right	0	0.039	0	1.0	
H2B	Deflection Front or Rear	0	0.051	0	1.0	
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5	
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5	
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11	
L1	Lead Wire Enclosure	0.09842	-	2.5	-	
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9	
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75	
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95	
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20	
T1	Overall Taped Package Thickness	-	0.0567	-	1.44	
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65	
W	Carrier Strip Width	0.6889	0.7481	17.5	19	
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3	
W2	Adhesive Tape Position	.0059	0.01968	0.15	0.5	

- 2. Maximum alignment deviation between leads not to be greater than 0.2 mm.
- 3. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
- 4. Component lead to tape adhesion must meet the pull test requirements.
- Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- 6. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
- 7. No more than 1 consecutive missing component is permitted.
- 8. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.
- 9. Splices will not interfere with the sprocket feed holes.

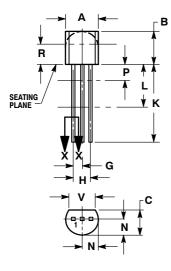
## ORDERING & SHIPPING INFORMATION: Packaging Options, Device Suffix

U.S.	Europe Equivalent	Shipping	Description of TO-92 Tape Orientation
	Z0103MARL1G	Radial Tape and Reel (2K/Reel)	Flat side of TO-92 and adhesive tape visible
Z0103MAG		Bulk in Box (5K/Box)	N/A, Bulk
Z0103MARLRPG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape visible
Z0103MARLRFG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape on reverse side
	Z0107MARL1G	Radial Tape and Reel (2K/Reel)	Flat side of TO-92 and adhesive tape visible
Z0107MAG		Bulk in Box (5K/Box)	N/A, Bulk
Z0107MARLRPG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape visible
Z0107MARLRFG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape on reverse side
	Z0109MARL1G	Radial Tape and Reel (2K/Reel)	Flat side of TO-92 and adhesive tape visible
Z0109MAG		Bulk in Box (5K/Box)	N/A, Bulk
Z0109MARLRPG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape visible
Z0109MARLRFG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape on reverse side

#### PACKAGE DIMENSIONS

## TO-92 (TO-226AA)

CASE 029-11 ISSUE AM



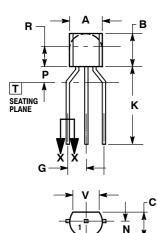
STRAIGHT LEAD **BULK PACK** 



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD** TAPE & REEL AMMO PACK



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
- CONTROLLING DIMENSION: MILLIMETERS.
  CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
_	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3 //3		

STYLE 12:

PIN 1. MAIN TERMINAL 1 2 GATE

3. MAIN TERMINAL 2

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